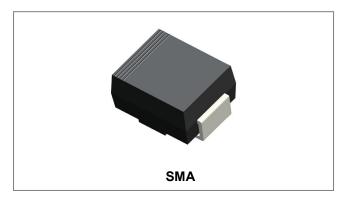






FR1A-FR1M 1.0A SURFACE MOUNT FAST RECOVERY RECTIFIER



Features

- · Fast switching for high efficiency
- Low leakage current
- · High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and
- WEEE 2002/96/EC
- · Glass passivated chip junction
- This is a Pb Free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-214AC molded plastic body over passivated chip
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- · Polarity: Color band denotes cathode end
- Mounting Position: AnyWeight: 0.07 grams

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	FR1A	FR1B	FR1D	FR1G	FR1J	FR1K	FR1M	Units
Peak Repetitive Reverse Voltage DC Blocking Voltage	V _{RRM} V _{DC}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current @T _A = 90°C	I _(AV)	1.0			А				
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30			А				
Forward Voltage @I _F =1.0A	V _{FM}	1.30			V				
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5.0 50.0			μA				
Reverse recovery time (Note 1)	trr	150 250 500		00	ns				
Typical Junction Capacitance (Note 2)	CJ	15			pF				
Typical Thermal Resistance (Note 3)	R _{0JA} R _{0JL}	100.0 32		°C/W					
Operating and Storage Temperature Range	T _{STG}	-55 to +150			°C				

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Mounted on 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas.
 - China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •







Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE

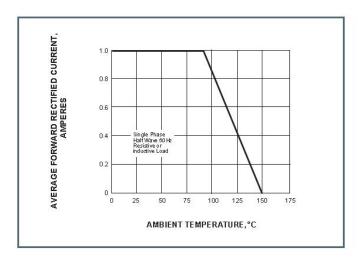


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

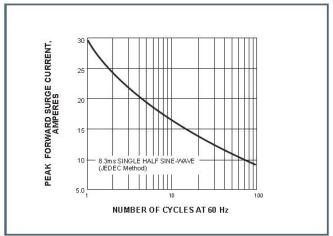


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

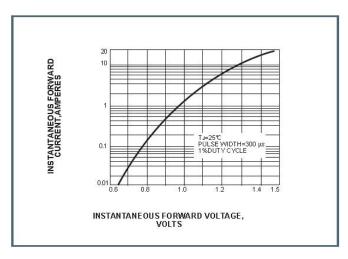
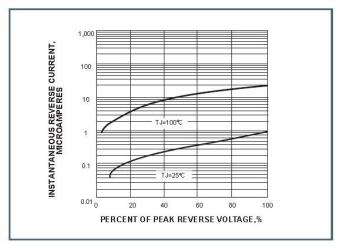


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



[•] China - Germany - Korea - Singapore - United States •

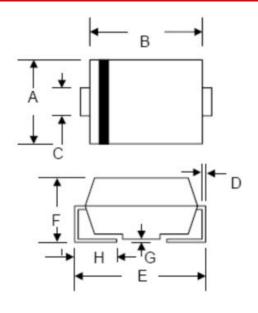
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Mechanical Dimensions SMA



SYMBOL	Millimeters			Inches			
STIVIBUL	Min.	Max.	Min.	Max.			
Α	2.40	2.84	0.094	0.112			
В	3.99	4.75	0.157	0.187			
С	1.05	1.70	0.041	0.067			
D	0.15	0.51	0.006	0.020			
E	4.80	5.66	0.189	0.223			
F	1.90	2.95	0.075	0.116			
G	0.05	0.203	0.002	0.008			
Н	0.76	1.52	0.030	0.600			

Ordering Information

Device	Package	Shipping
FR1A-FR1M	SMA	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

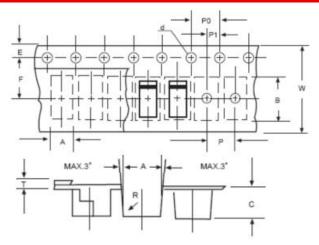


Where XXXXX is YYWWL

FR1A = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape & Reel Specification SMA



SYMBOL	Millimeters			
STWIBUL	Min.	Max.		
Α	2.97	3.17		
В	5.70	5.90		
С	2.32	2.52		
d	1.40	1.60		
Е	1.40	1.60		
F	5.60	5.70		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
Т	0.25	0.35		
W	11.80	12.20		

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